Sheet 1 of 1

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)

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ATTY. DOCKET NO.	SERIAL NO.
1035-501	10/802,735
APPLICANT	
TAKAFUJI et al	
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

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	TT	Vandooren et al, "Scaling Assessment of Fully-Depleted SOI Technology at the 30nm Gate Length Generation", 2002 IEEE international SOI Conference Proceedings, October 2002, pp. 25-27

*Examiner		Date Considered	12/01/2004

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

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